WHAT IS CLAIMED IS:

1. A side-emission type semiconductor light-emitting device, comprising:

a substrate formed with an electrode;

an LED chip bonded onto said electrode; and

a transparent or translucent resin with which said LED chip is molded, wherein said transparent or translucent resin has a light-emitting surface formed by a roughened surface being perpendicular to said substrate.

2. A side-emission type semiconductor light-emitting device according to claim 1, wherein said light-emitting surface is formed by dicing.

3. A manufacturing method of a side-emission type semiconductor light-emitting device, comprising the following steps of:

(a) mounting two reflectors having openings opposed with each other on a substrate mounted with an LED chip;

(b) injecting a transparent or translucent resin at an opposing portion of said openings; and

(c) dicing said transparent or translucent resin being hardened and said substrate at said opposing portion.

4. A side-emission type semiconductor light-emitting device, comprising:

a substrate formed with an electrode;

an LED chip bonded onto said substrate;

a transparent or translucent resin with which said LED chip is molded; and

a reflector which reflects a light emitted from said LED chip, wherein said transparent or translucent resin has a convex portion, and said reflector has a concave portion to be fitted into said convex portion.

5. A side-emission type semiconductor light-emitting device according to claim 4,

wherein said concave portion is a throughole having a diameter which becomes larger from one main surface to other main surface of said reflector.

6. A side-emission type semiconductor light-emitting device according to claim 5, wherein said one main surface is a surface brought into contact with said transparent or translucent resin, and said other main surface is a surface exposed to outside.

7. A side-emission type semiconductor light-emitting device according to any one of claims 4 to 6, wherein said LED chip has a bonding wire extending from a top surface, and said concave portion is formed directly above said LED chip.

8. A manufacturing method of a side-emission type semiconductor light-emitting device, comprising the following steps of:

(a) mounting a reflector formed with a concave portion on a substrate;

(b) removing an organic matter adhering to a surface, including an inner surface of said concave portion, of said reflector; and

(c) injecting a transparent or translucent resin between said reflector and said substrate up to said concave portion.

9. A manufacturing method of a side-emission type semiconductor light-emitting device according to claim 8, wherein said reflector is subjected to UV cleaning in the step (b).

10. A side-emission type semiconductor light-emitting device, comprising:

a substrate formed with an electrode; and

an LED chip which is bonded onto said electrode by a bonding paste, wherein said LED chip has a transparent or translucent base and a light-emitting layer formed thereon, and is mounted on a position deviated from an application position of said bonding paste to a light emitting surface side.

11. A side-emission type semiconductor light-emitting device according to claim 10, wherein said electrode includes an application area having a center deviated from a mounted position of said LED chip to an opposite direction of said light-emitting surface.

12. A side-emission type semiconductor light-emitting device according to claim 11, wherein said electrode further includes an auxiliary area formed closer to said light-emitting surface side than said application area and a narrow connecting portion connecting said application area and said auxiliary area.

13. A side-emission type semiconductor light-emitting device according to claim 11 or 12, wherein a center of said application area is deviated from a center of said substrate to said opposite direction.